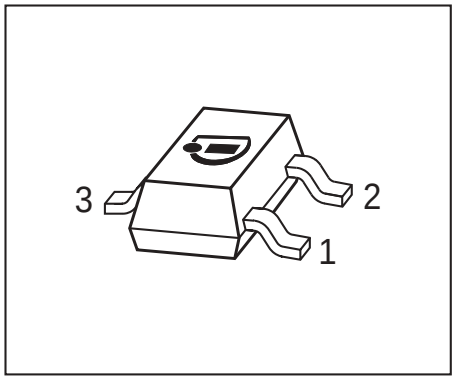
NPN Silicon Switching Transistor



- Low collector-emitter saturation voltage
- Complementary type: SMBT2907AW (PNP)
- Pb-free (RoHS compliant) package[1)]
- Qualified according AEC Q101

AEC Qualified RoHS

Type	Marking	Pin Configuration			Package
SMBT2222A/MMBT2222A	s1P	1 = B	2 = E	3 = C	SOT23

Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CEO}	40	V
Collector-base voltage	V_{CBO}	75	
Emitter-base voltage	V_{EBO}	6	
Collector current	I_C	600	mA
Total power dissipation- $T_S \leq 77$ °C	P_{tot}	330	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-65 ... 150	

Thermal Resistance

Parameter	Symbol	Value	Unit
Junction - soldering point[2)]	R_{thJS}	≤ 220	K/W

[1]Pb-containing package may be available upon special request
[2]For calculation of R_{thJA} please refer to Application Note Thermal Resistance

Electrical Characteristics at T_A = 25°C, unless otherwise specified

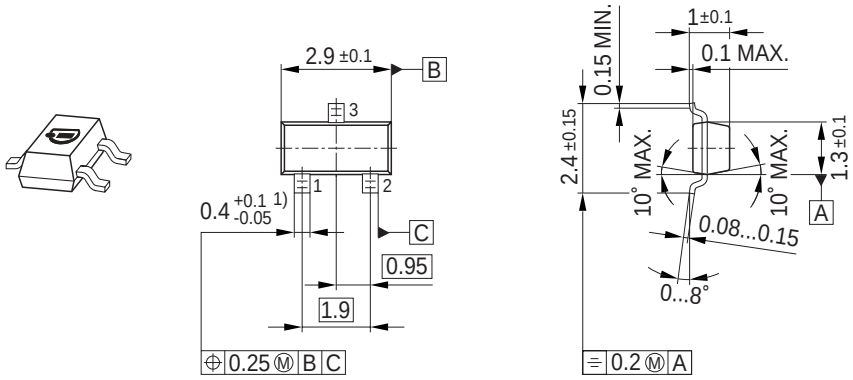
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
DC Characteristics					
Collector-emitter breakdown voltage I_C = 10 mA, I_B = 0	$V_{(BR)CEO}$	40	-	-	V
Collector-base breakdown voltage I_C = 10 µA, I_E = 0	$V_{(BR)CBO}$	75	-	-	
Emitter-base breakdown voltage I_E = 10 µA, I_C = 0	$V_{(BR)EBO}$	6	-	-	
Collector-base cutoff current	I_{CBO}				µA
V_{CB} = 60 V, I_E = 0		-	-	0.01	
V_{CB} = 60 V, I_E = 0 , T_A = 150 °C		-	-	10	
Emitter-base cutoff current V_{EB} = 3 V, I_C = 0	I_{EBO}	-	-	10	nA
DC current gain[1)]	h_{FE}				-
I_C = 100 µA, V_{CE} = 10 V		35	-	-	
I_C = 1 mA, V_{CE} = 10 V		50	-	-	
I_C = 10 mA, V_{CE} = 10 V		75	-	-	
I_C = 150 mA, V_{CE} = 1 V		50	-	-	
I_C = 150 mA, V_{CE} = 10 V		100	-	300	
I_C = 500 mA, V_{CE} = 10 V		40	-	-	
Collector-emitter saturation voltage[1)]	V_{CEsat}				V
I_C = 150 mA, I_B = 15 mA		-	-	0.3	
I_C = 500 mA, I_B = 50 mA		-	-	1	
Base emitter saturation voltage[1)]	V_{BEsat}				
I_C = 150 mA, I_B = 15 mA		0.6	-	1.2	
I_C = 500 mA, I_B = 50 mA		-	-	2	

[1]Pulse test: t < 300µs; D < 2%

Electrical Characteristics at T_A = 25°C, unless otherwise specified

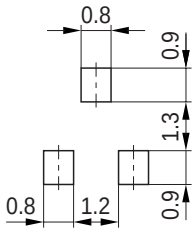
Parameter	Symbol	Values			Unit
		min.	typ.	max.	
AC Characteristics					
Transition frequency I_C = 20 mA, V_{CE} = 20 V, f = 100 MHz	f_T	300	-	-	MHz
Collector-base capacitance V_{CB} = 10 V, f = 1 MHz	C_{cb}	-	2.5	5	pF
Emitter-base capacitance V_{EB} = 0.5 V, f = 1 MHz	C_{eb}	-	-	35	
Short-circuit input impedance I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz I_C = 10 mA, V_{CE} = 10 V, f = 1 kHz	h_{11e}	 2 0.25	 - -	 8 1.25	kΩ
Open-circuit reverse voltage transf. ratio I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz I_C = 10 mA, V_{CE} = 10 V, f = 1 kHz	h_{12e}	 - -	 - -	 8 4	10^{-4}
Short-circuit forward current transf. ratio I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz I_C = 10 mA, V_{CE} = 10 V, f = 1 kHz	h_{21e}	 50 75	 - -	 300 375	-
Open-circuit output admittance I_C = 1 mA, V_{CE} = 10 V, f = 1 kHz I_C = 10 mA, V_{CE} = 10 V, f = 1 kHz	h_{22e}	 5 25	 - -	 35 200	µS
Delay time V_{CC} = 30 V, I_C = 150 mA, I_{B1} = 15 mA, $V_{BE(off)}$ = 0.5 V	t_d	-	-	10	ns
Rise time V_{CC} = 30 V, I_C = 150 mA, I_{B1} = 15 mA, $V_{BE(off)}$ = 0.5 V	t_r	-	-	25	
Storage time V_{CC} = 30 V, I_C = 150 mA, I_{B1} = I_{B2} = 15mA	t_{stg}	-	-	225	
Fall time V_{CC} = 30 V, I_C = 150 mA, I_{B1} = I_{B2} = 15mA	t_f	-	-	60	
Noise figure I_C = 100 µA, V_{CE} = 10 V, f = 1 kHz, Δf = 200 Hz, R_S = 1 kΩ	F	-	-	4	dB

Package Outline

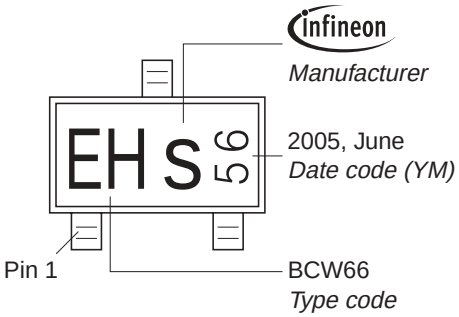


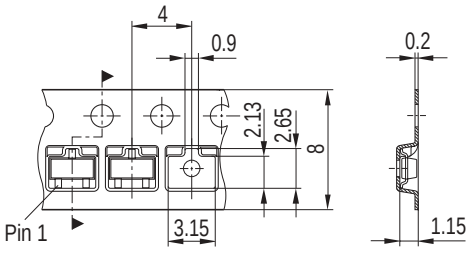
1) Lead width can be 0.6 max. in dambar area

Foot Print



Marking Layout (Example)



Standard Packing

Reel ø180 mm = 3.000 Pieces/Reel
Reel ø330 mm = 10.000 Pieces/Reel